

PSMN4R3-80PS

N-channel 80 V, 4.3 m Ω standard level MOSFET in TO220 Rev. 03 — 18 April 2011 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switch

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	80	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	[2]	-	3.7	4.3	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A;}$ $T_j = 100 \text{ °C; see } Figure 12$	[2]	-	6.1	7.1	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$	-	28.4	-	nC
$Q_{G(tot)}$	total gate charge	V _{DS} = 40 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	111	-	nC
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; unclamped	-	-	676	mJ

- [1] Continuous current is limited by package
- [2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source	205	G (EA)
mb	D	drain		mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R3-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

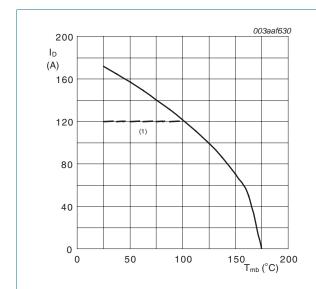
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		3 , (
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	80	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V; } T_{mb} = 100 \text{ °C; see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	120	Α
		$V_{GS} = 10 \text{ V; } T_{mb} = 25 \text{ °C; see } \frac{\text{Figure 1}}{}$	<u>[1]</u>	-	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3		-	688	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drai	n diode					
Is	source current	T _{mb} = 25 °C	[1]	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	688	Α
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le$ 80 V; R_{GS} = 50 Ω ; unclamped		-	676	mJ

[1] Continuous current is limited by package



 $V_{\it GS} \geq$ 10 V; (1) capped at 120 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature

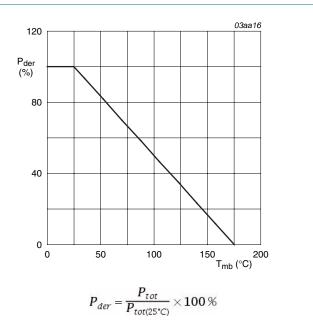
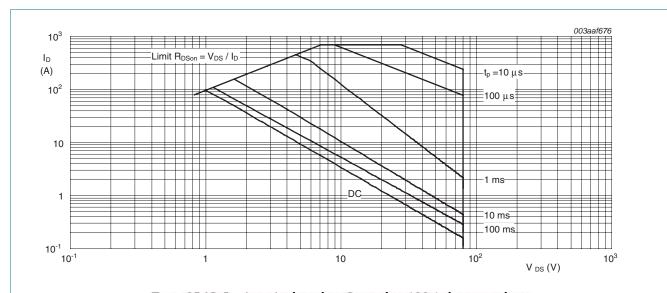


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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 T_{mb} = 25 °C; I_{DM} is a single pulse; Capped at 120 A due to package

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

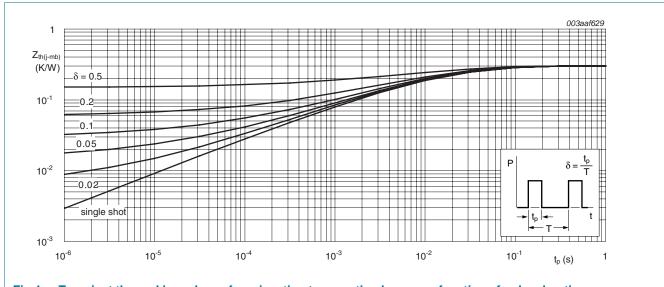


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	73	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see <u>Figure 10</u>	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	[1] -	8.9	10.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	[1] -	3.7	4.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	[1] -	6.1	7.1	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	104	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	111	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	38	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	24.1	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	14.1	-	nC
Q _{GD}	gate-drain charge		-	28.4	-	nC
V _{GS(pI)}	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 40 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	6.1	-	V
C _{iss}	input capacitance	V _{DS} = 40 V; V _{GS} = 0 V; f = 1 MHz;	-	8161	-	pF
Coss	output capacitance	$T_j = 25 \text{ °C}$; see <u>Figure 16</u>	-	701	-	pF
C _{rss}	reverse transfer capacitance		-	337	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 0.53 \Omega; V_{GS} = 10 \text{ V};$	-	38	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; I_D = 75 A$	-	29	-	ns
t _{d(off)}	turn-off delay time		-	94	-	ns
t _f	fall time		-	33	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 17	-	-	1.2	V	
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$;	-	59	-	ns	
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	109	-	nC	

[1] Measured 3 mm from package.

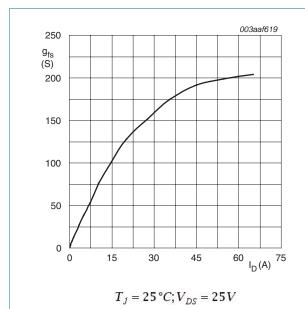


Fig 5. Forward transconductance as a function of drain current; typical values

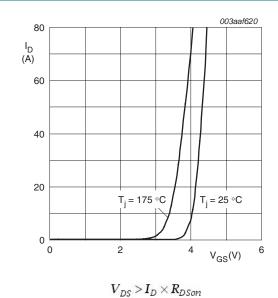
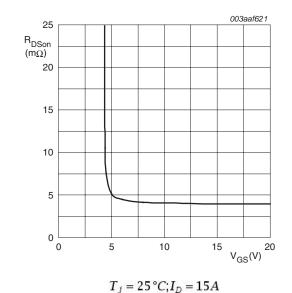


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



Drain-source on-state resistance as a function Fig 7. of gate-source voltage; typical values

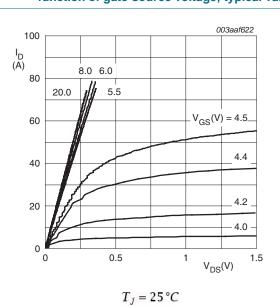


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values

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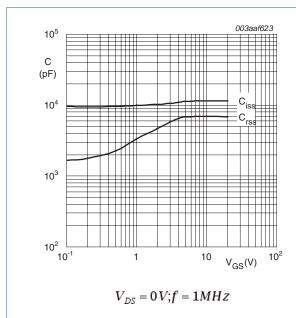


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

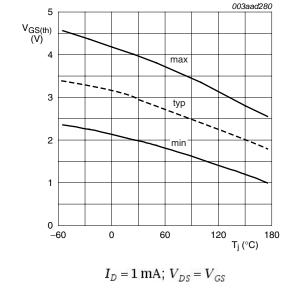


Fig 10. Gate-source threshold voltage as a function of junction temperature

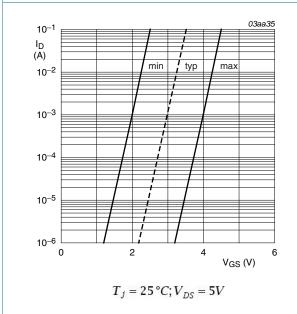


Fig 11. Sub-threshold drain current as a function of gate-source voltage

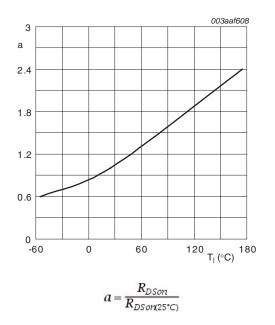
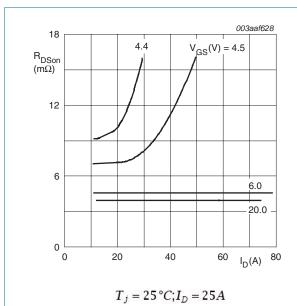


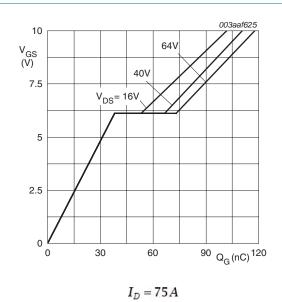
Fig 12. Normailzed drain-source on-state resistance factor as a function of junction temperature



V_{DS} — I_D V_{GS(pl)} V_{GS(th)} V_{GS} Q_{GS1} Q_{GS2} Q_{G(tot)} 003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions



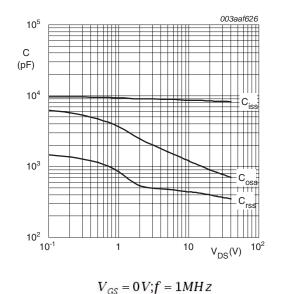


Fig 15. Gate-source voltage as a function of gate charge; typical values



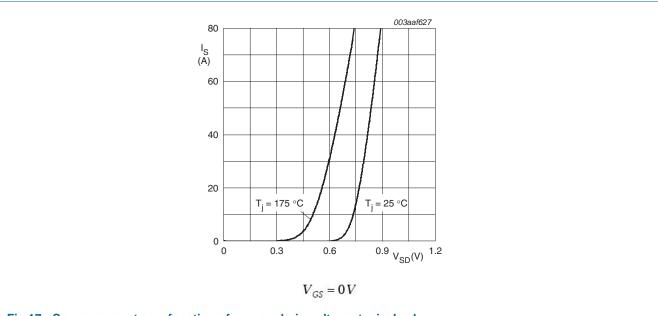
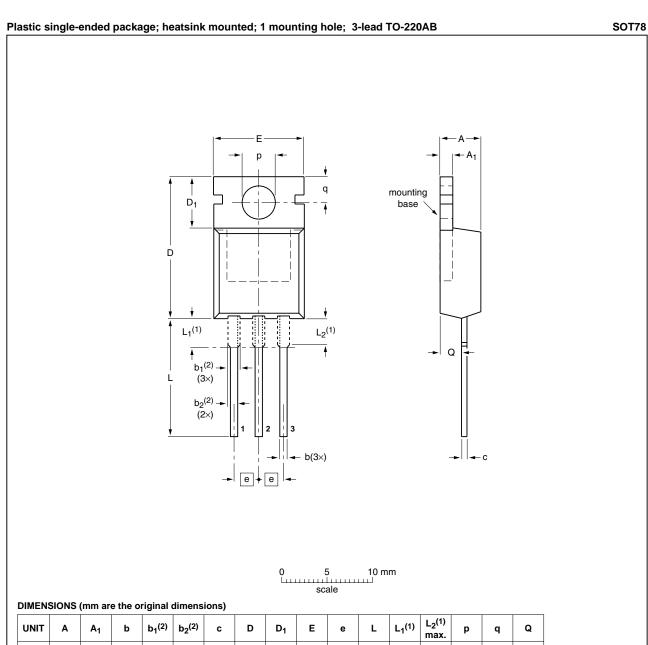


Fig 17. Source current as a function of source-drain voltage; typical values

Package outline



UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13	

Fig 18. Package outline SOT78 (TO-220AB)

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Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PSMN4R3-80PS v.3	20110418	Product data sheet	-	PSMN4R3-80PS v.2		
Modifications: • Status changed from objective to product.						
	 Various changes to content. 					
PSMN4R3-80PS v.2	20110309	Objective data sheet	-	PSMN4R3-80PS v.1		

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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